

TIC106A, TIC106B, TIC106C, TIC106D, TIC106E, TIC106M, TIC106N, TIC106S

P-N-P-N SILICON REVERSE-BLOCKING TRIODE THYRISTORS

- 5 A Continuous On-State Current
- 30 A Surge-Current
- Glass Passivated Wafer
- 100 V to 800 V Off-State Voltage
- Max I_{GT} of 200 μA
- Compliance to ROHS

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value							Unit	
		Α	в	С	D	Е	М	S	Ν	
V _{DRM}	Repetitive peak off-state voltage (see Note1)	100	200	300	400	500	600	700	800	V
V _{RRM}	Repetitive peak reverse voltage	100	200	300	400	500	600	700	800	V
I _{T(RMS)}	Continuous on-state current at (or below) 80°C case temperature (see note2)	5						А		
I _{T(AV)}	Average on-state current (180° conduction angle) at(or below) 80°C case temperature (see Note3)						А			
I _{TM}	Surge on-state current (see Note4)	30					Α			
I _{GM}	Peak positive gate current (pulse width ≤300 µs)	0.2				А				
Р _{GM}	Peak power dissipation (pulse width ≤300 µs)	1.3					W			
P _{G(AV)}	Average gate power dissipation (see Note5)	0.3				W				
Tc	Operating case temperature range	-40 to +110				°C				
T _{stg}	Storage temperature range	-40 to +125				°C				
TL	Lead temperature 1.6 mm from case for 10 seconds	230				°C				

Notes:

1. These values apply when the gate-cathode resistance $R_{GK} = 1k\Omega$

2. These values apply for continuous dc operation with resistive load. Above 80°C derate linearly to zero at 110°C.

3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 80°C derate linearly to zero at 110°C.

4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

5. This value applies for a maximum averaging time of 20 ms.

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THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
t _{gt}	Gate-controlled $V_{AA} = 30 \text{ V}, \text{ R}_L = 6 \Omega, \text{ R}_{GK(eff)} = 50 \text{ V}$ Turn-on time $V_{in} = 50 \text{ V}$	^{5 kΩ,} 1.75	116
t _q	$ \begin{array}{ c c c } \mbox{Circuit-communicated} \\ \mbox{Turn-off time} \end{array} V_{AA} = 30 \ V, \ R_L = 6 \ \Omega, \ I_{RM} \approx 8 \ A \end{array} $	7.7	μs
R _{∂JC}		≤ 3.5	°C/W
R∂JA		≤ 62.5	0///

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Тур	Мx	Unit	
I _{DRM}	Repetitive peak off-state current	V_D = Rated V_{DRM} , R_{GK} = 1 k Ω , T _C = 110°C	-	-	400	μA	
I _{RRM}	Repetitive peak reverse current	V_R = Rated V_{RRM} , I_G = 0, T_C = 110°C	-	-	1	mA	
I _{GT}	Gate trigger current	V_{AA} = 6 V, R _L = 100 Ω, t _{p(g)} ≥ 20µs	-	60	200	μA	
V _{GT}	Gate trigger voltage	V_{AA} = 6 V, R _L = 100 Ω, R _{GK} = 1 kΩ, t _{p(g)} ≥ 20µs, T _C = -40°C	-	-	1.2	2	
		V _{AA} = 6 V, R _L = 100 Ω, R _{GK} = 1 kΩ, t _{p(α)} ≥ 20μs,	0.4	0.6	1	V	
		V_{AA} = 6 V, R _L = 100 Ω, R _{GK} = 1 kΩ, t _{p(g)} ≥ 20µs, T _C = 110°C	0.2	-	-		
I _H	Holding current	$\label{eq:VAA} \begin{array}{llllllllllllllllllllllllllllllllllll$	-	-	5		
		$V_{AA} = 6$ V, $R_{GK} = 1$ k Ω , initiating $I_T = 10$ mA, $T_C = -40^{\circ}C$	-	-	8	mA	
V _{TM}	Peak on-state voltage	I _{TM} = 5A (see Note6)	-	-	1.7	V	
dv/dt	Critical rate of rise of off-state voltage	V_D = Rated V_D , R_{GK} = 1 k Ω , T _C = 110°C	-	10	-	V/µs	

Note 6:

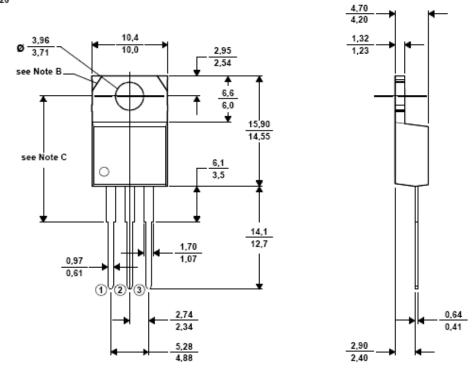
This parameters must be measured using pulse techniques, $t_w = 300 \mu s$, duty cycle ≤ 2 %, voltage-sensing contacts, separate from the courrent-carrying contacts, are located within 3.2mm (1/8 inch) from de device body.

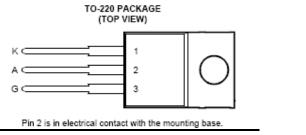


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MECHANICAL DATA CASE TO-220

TO220





Pin 1 :	kathode
Pin 2 :	Anode
Pin 3 :	Gate

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